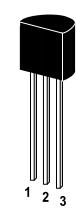
## **PNP Silicon Epitaxial Planar Transistor**

for switching and AF amplifier applications.

The transistor is subdivided into two groups, O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base TO-92 Plastic Package Weight approx. 0.19g

## Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	-V <sub>CBO</sub>	35	V
Collector Emitter Voltage	-V <sub>CEO</sub>	30	V
Emitter Base Voltage	-V <sub>EBO</sub>	5	V
Collector Current	-I <sub>C</sub>	800	mA
Emitter Current	Ι <sub>Ε</sub>	800	mA
Power Dissipation	P <sub>tot</sub>	600	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







Dated : 07/12/2002

## ST 2SA1271

## Characteristics at T<sub>amb</sub>=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at -V <sub>CE</sub> =1V, -I <sub>C</sub> =100mA					
Current Gain Group O	h <sub>FE</sub>	100	-	200	-
Y	h <sub>FE</sub>	160	-	320	-
at $-V_{CE}=1V$ , $-I_{C}=700$ mA	h <sub>FE</sub>	35	-	-	-
Collector Cutoff Current					
at -V <sub>CB</sub> =35V	-I <sub>CBO</sub>	-	-	0.1	μA
Emitter Cutoff Current					
at -V <sub>EB</sub> =5V	-I <sub>EBO</sub>	-	-	0.1	μA
Collector Emitter Saturation Voltage					
at -I <sub>C</sub> =500mA, -I <sub>B</sub> =20mA	-V <sub>CE(sat)</sub>	-	-	0.7	V
Transition Frequency					
at -V <sub>CE</sub> =5V, -I <sub>C</sub> =10mA	f⊤	-	120	-	MHz
Base Emitter Voltage					
at -I <sub>C</sub> =10mA, -V <sub>CE</sub> =1V	-V <sub>BE</sub>	0.5	-	0.8	V
Collector Output Capacitance					
at -V <sub>CB</sub> =10V, f=1MHz	C <sub>OB</sub>	-	19	-	pF
Collector Emitter Breakdown Voltage					
at -I <sub>c</sub> =10mA	-V <sub>CEO</sub>	30	-	-	V







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